

KTA1042D TRANSISTOR (PNP)

FEATURES

Low Collector-Emitter Saturation Voltage

APPLICATIONS

General Purpose Application



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-100	V
V _{CEO}	Collector-Emitter Voltage	-100	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current	-5	Α
Pc	Collector Power Dissipation	1.25	W
R _{0JA}	Thermal Resistance from Junction to Ambient	100	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}$

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO} *	I _C =-1mA ,I _E =0	-100			V
Collector-emitter breakdown voltage	V _(BR) CEO*	I _C =-50mA, I _B =0	-100			V
Emitter-base breakdown voltage	V _{(BR)EBO} *	$I_E=-1mA,I_C=0$	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-100V,I _E =0			-100	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V,I _C =0			-1	mA
DC ourrent gain	h _{FE(1)}	V _{CE} =-5V, I _C =-1A	70		240	
DC current gain	h _{FE(2)}	V _{CE} =-5V, I _C =-4A	20			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-4A,I _B =-0.4A			-2	V
Base-emitter voltage	V_{BE}	V _{CE} =-5V, I _C =-4A			-1.5	V
Transition frequency	f _T	V _{CE} =-5V ,I _C =-1A		30		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V ,I _E =0,f=1MHz			270	рF

^{*} Pulse test

CLASSIFICATION OF h_{FE(1)}

Rank	0	Υ
Range	70-140	120-240



